

2.5A 5V E-Fuse with Bi-Directional Protection Switch and DevSleep/Disable Mode

Description

The LX8233 is a fast acting bi-directional eFuse switch designed both to protect circuitry connected to its output (VOUT) from transient input voltage surges on its input (VCC), and to protect VCC from overload current events coming from the load on VOUT. It will also block the reverse discharge current from flowing from VOUT to VCC if the input supply collapses.

Voltage protection features include under-voltage lockout (UVLO), and over-voltage clamping. This clamp limits VOUT voltage allowing continued circuit operation during an input over-voltage transient condition, while UVLO ensures that VOUT remains off until VCC reaches its minimum operating threshold. On the current side, the LX8233 protects the input from a output short circuit and/or over current condition with a 2.5A current limit circuit.

Another protection feature is latching thermal shutdown of VOUT, with a fault flag output on the combined EN/FAULT pin. Once thermal shutdown threshold is reached and the eFuse switch opens, the tristate EN/FAULT pin will be pulled to about 1.6V signaling to the system and potentially other connected eFuse switches that a fault has occurred. The LX8233 latches at this level until reset by the Enable pin, DEVSLP pin, or there is a VCC power recycle.

At device power up the user can initialize the DevSleep pin functionality and VOUT slew rate in one of two modes depending on the state of the FET_ON pin. In DevSleep Disabled Mode the slew rate is set to 13ms, and VOUT shutdown is engaged when the DEVSLP pin is toggled high regardless of the state of the FET_ON pin. In DevSleep Enabled Mode the slew rate is reduced to 1.4ms, and shutdown is engaged when the DEVSLP pin is toggled high and the FET_ON pin is low.

Features

- 50mΩ (typ.) Rdson Internal eFuse FET Protected From 15V
- Bi-directional Current Blocking Switch
- SATA DevSleep Support
- SAS-DISABLE Support
- Up to 15V Transient Input Range
- 6V Output Voltage Clamp
- Continuous Operation During VCC surge
- Current Limit at Overload and Short-Circuit Protection
- Over-Temperature Protection
- Selectable Soft-start 13ms or 1.4ms Risetime
- UVLO Detection
- VQFN 2mm x 3mm 13L Package

Applications

- Hard-Disk Drive
- Solid-State Drive
- Hot Swap
- PC Cards

Pin Configuration and Pinout

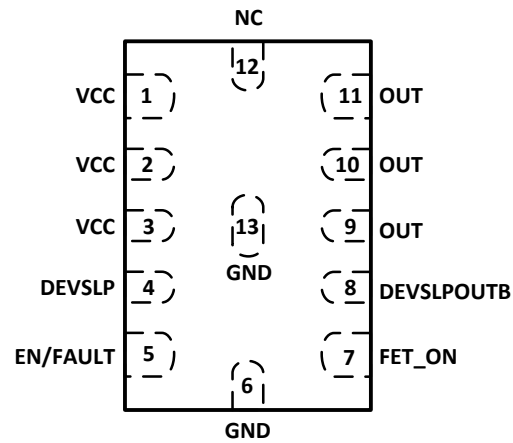


Figure 3 · Pinout VQFN 2mm x 3mm 13L Top View

Marking: Line 1 MSC
Line 2 8233
Line 3 Date / Lot Code

Ordering Information

Ambient Temperature	Type	Package	Part Number	Packaging Type
-40°C to 85°C	RoHS Compliant, Pb-free	VQFN 2mm x 3mm 13L	LX8233ILQ	Bulk / Tube
			LX8233ILQ-TR	Tape and Reel

Pin Description

Pin Number	Pin Designator	Input/Output	Description												
1, 2, 3	VCC	Input	Input of the device.												
4	DEVSLP	Input	<p>DevSleep mode input. There are two modes for the usage of DEVSLP. One operational mode is <u>DEVSLP Enable Mode</u>. It is selected by connecting the FET_ON pin of LX8233 to SOC <i>during power on initialization</i>. In this mode, only when FET_ON is low will setting DEVSLP high shut down the LX8233. This handshake feature allows the SOC to override the shutdown process initiated by the host using DevSleep allowing any necessary housekeeping functions to complete before powering off the switch. When in this mode the VOUT softstart time is programmed to 1.4 ms.</p> <p>The other mode is <u>DEVSLP Disabled Mode</u>. This is selected by letting FET_ON pin float <i>during power on initialization</i>. In this mode the LX8233 will shutdown by setting DEVSLP high regardless of the FET_ON state. When in this mode the VOUT softstart time is programmed to 13 ms.</p> <p>The two mode are summarized in the table below.</p> <table border="1" data-bbox="712 865 1417 1043"> <thead> <tr> <th></th> <th>DEVSLP Disabled</th> <th>DEVSLP Enabled</th> </tr> </thead> <tbody> <tr> <td>FET_ON</td> <td>Float</td> <td>Connected to SOC</td> </tr> <tr> <td>T_{RISE}</td> <td>~13ms</td> <td>~1.4ms</td> </tr> <tr> <td>Shutdown</td> <td>DEVSLP High</td> <td>(DEVSLP High) AND (FET_ON Low)</td> </tr> </tbody> </table>		DEVSLP Disabled	DEVSLP Enabled	FET_ON	Float	Connected to SOC	T _{RISE}	~13ms	~1.4ms	Shutdown	DEVSLP High	(DEVSLP High) AND (FET_ON Low)
	DEVSLP Disabled	DEVSLP Enabled													
FET_ON	Float	Connected to SOC													
T _{RISE}	~13ms	~1.4ms													
Shutdown	DEVSLP High	(DEVSLP High) AND (FET_ON Low)													
5	EN/FAULT	Input/Output	The EN/FAULT pin is a tri-state, bidirectional interface. It can be used to disable the output of the device by pulling it to ground using an open drain or open collector device. If a thermal fault occurs, the voltage on this pin will go to an intermediate state (~1.6V) to signal a monitoring circuit that the device is in thermal shutdown. It can also be connected to another device in this family to cause a simultaneous shutdown during thermal events. See simplified schematic in Theory of Operation/ Application section.												
6	GND	-	Ground Pin (Pin 6 and Pin 13 are internally connected).												
7	FET_ON	Input	<p>DEVSLP mode is configured by the FET_ON state during power on initialization.</p> <p>When FET_ON is floating (50pf maximum pin capacitance), the LX8233 is set to DEVSLP Disabled Mode. In this mode, the LX8233 can be shut down by setting the DEVSLP pin high.</p> <p>When FET_ON is connected to SOC, the LX8233 can only be shut down by setting both DEVSLP high and FET_ON low.</p>												
8	DEVSLPOUTB	Output	Open-drain output. A pull-up resistor is connected to the I/O supply of SOC. DEVSLPOUTB is the inversed polarity version of DEVSLP.												
9, 10, 11	VOUT	Output	Output of the device, connect to circuitry to be protected. A 10uF capacitor is needed for over voltage protection stability. The capacitor return should be connected directly to the GND pin.												
12	NC	-	Do Not Connect.												
13	GND	-	Ground Pin(Pin 6 and Pin 13 are internally connected).												

Block Diagram

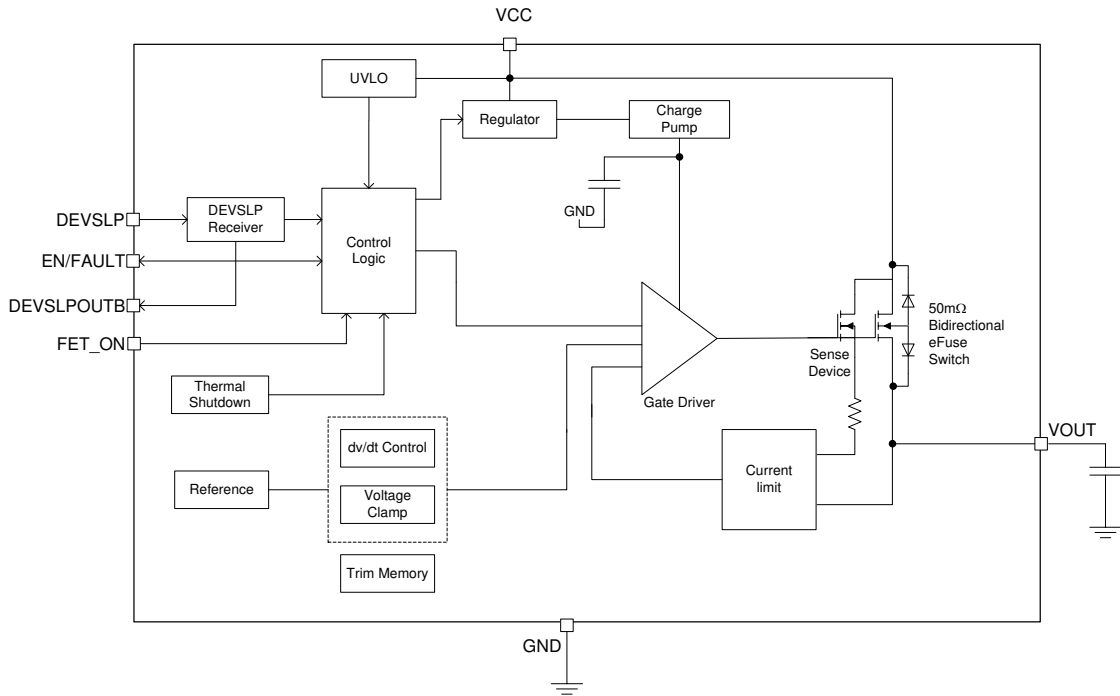


Figure 4 · Simplified Block Diagram of LX8233

Absolute Maximum Ratings

Parameter	Min	Max	Units
VCC to GND (Steady-State)	-0.3	15	V
VCC to GND (Transient 100ms)	-0.3	15	V
VOUT to GND (Steady-State)	-0.3	6.5	V
VOUT to GND (Transient 100ms)	-0.3	7	V
EN/FAULT to GND	-0.3	≤VCC	V
EN/FAULT to GND	-0.3	6	V
DEVSLPOUTB to GND	-0.3	6	V
DEVSLP to GND	-0.3	3.6	V
FET_ON to GND	-0.3	3.6	V
ESD (Human Body Model)	2000		V
ESD (Charged Device Model)	1000		V
Power Dissipation		1.3	W
Storage Temperature	-65	150	°C

Note: Performance is not necessarily guaranteed over this entire range. These are maximum stress ratings only. Exceeding these ratings, even momentarily, can cause immediate damage, or negatively impact long-term operating reliability

Operating Ratings

	Min	Max	Units
VCC	4.2	5.75	V
I(VCC)		2.5	A
Junction Temperature	-40	125	°C

Note: Performance is generally guaranteed over this range as further detailed below under Electrical Characteristics.

Thermal Properties

Thermal Resistance	Typ	Units
θ_{JA}	40	°C/W

Note: The θ_{JA} numbers assume no forced airflow. Junction Temperature is calculated using $T_J = T_A + (PD \times \theta_{JA})$. In particular, θ_{JA} is a function of the PCB construction. The stated number above is for a four-layer board in accordance with JESD-51 (JEDEC).

Electrical Characteristics

Note: The following specifications apply over the operating ambient temperature of $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$ except where otherwise noted with the following test conditions: $V_{CC} = 5\text{V}$. Typical parameter refers to $T_J = 25^{\circ}\text{C}$.

Symbol	Parameters	Test Conditions/Comments	Min	Typ	Max	Units
eFuse FET						
T_{ONDLY}	Turn-on Delay Time	Enable by EN/FAULT with load current 100mA.		80		μs
R_{DSON}	On Resistance	$T_A = 25^{\circ}\text{C}$, (Note 2)		50		$\text{m}\Omega$
		$T_J = 80^{\circ}\text{C}$, (Note 1)		95		$\text{m}\Omega$
I_{OFF}	Off State Output Leakage Current	$V_{CC} = 12V_{\text{DC}}$, EN/FAULT = GND, VOUT = GND Measure I(VOUT)			1	μA
I_{DC}	Continuous Current	$T_A = 25^{\circ}\text{C}$		2		A
T_{RISE}	VOUT Rise Time	FET_ON = Float	10.4	13	15.6	ms
		FET_ON = GND		1.4		ms
Thermal Shutdown						
T_{SD}	Shutdown Temperature	OUT is latched off once thermal shutdown is triggered. It can be reset three ways. 1) EN/FAULT is pulled low then let float. 2) DEVSLP pin is toggled high then low. 3) VCC is recycled.		135		$^{\circ}\text{C}$
Under/Over Voltage Protection						
V_{CLAMP}	Output Clamping Voltage	$V_{CC} = 10\text{V}$	5.75		6.25	V
	Maximum Overshoot During Transient	V_{CC} transient from 5V to the higher than 12V at $100\text{V}/\mu\text{s}$ with $I_{\text{VOUT}} = 0\text{A}$. $C_{\text{OUT}} = 33\mu\text{F}$			6.5	V
	Minimum Undershoot During Transient	V_{CC} transient from 5V to the higher than 12V at $100\text{V}/\mu\text{s}$ with $I(\text{VOUT}) = 2.5\text{A}$. $C_{\text{OUT}} = 33\mu\text{F}$	4.5			V
$V_{\text{UVLO_TH}}$	Under-Voltage Lock-Out Threshold	Turn-on and voltage increases	3.75		4.2	V
$V_{\text{UVLO_HYS}}$	Under-Voltage Lock-Out Hysteresis			0.3		V
	Under-Voltage Lock-Out Response Time			2		μs
Current Protection						
$I_{\text{SC_LIM}}$	Short Circuit Current Limit	VOUT is $<1\text{V}$ from GND.		2.5		A
$I_{\text{AVG_LIM}}$	Overloading Current Limit	VOUT is 0.5V lower than the nominal VOUT.	2.5	3		A

Symbol	Parameters	Test Conditions/Comments	Min	Typ	Max	Units
Reverse Current Detection						
I _{reverse}	Reverse Current Limit		0.9	1.32	2.1	A
t _{reverse}	Reverse Current Limit Response Time	VCC DV/DT = -5V/1ms		2		μs
DEVSLP						
DEVSLP _{TH}	Logic Input Threshold	Measure the threshold	0.8		2.0	V
DEVSLP _{HYS}	Logic Input Hysteresis	Measure the threshold of DEVSLP		190		mV
DEVSLP _{MAX}	Maximum DEVSLP Pin Voltage	Design target. No test.			3.3	V
DEVSLP-Ω _{IN}	Input Impedance	Output Enabled, Unconnected pin = Enabled. Internal pull-down resistor test. Measure the impedance from DEVSLP to GND	350	500	1000	kΩ
DEVSLP-OFF-TDLY	Turn-off Deglitch Delay	100mA VOUT load. Logic Turn off by changing DEVSLP from 0V to 5V. Measure the delay from the edge of DEVSLP to 4.5V(the 10% lower to 5V VOUT).	2		50	μs
DEVSLP-ON-TDLY	Turn-on Deglitch Delay	100mA VOUT load. Logic Turn on by changing DEVSLP from 5V to 0V. Measure the delay from the edge of DEVSLP to 0.5V(the 10% of 5V VOUT).	2		300	μs
EN/FAULT						
VEN _{DISIL}	Disable Logic Input Level Low	Output disabled			0.4	V
VEN _{MIDIL}	Thermal Fault Input Logic Level Low	EN/FAULT pin is driven by the other eFuse. Thermal Fault, Output Disabled,			1.0	V
VEN _{MIDIH}	Thermal Fault Input Logic Level Low	EN/FAULT pin is driven by the other eFuse. Thermal Fault, Output Disabled,	2.1			V
VEN _{ENIH}	Enable Logic Input Level High	Output Enabled	3.3			V
	High State Max Voltage	(Note 1)			5.2	V
VEN _{MIDOL}	Thermal Fault Output Logic Level Low	LX8233 drives EN/FAULT pin. Thermal Fault, Output Disabled,	1.1			V
VEN _{MIDOH}	Thermal Fault Output Logic Level Low	LX8233 drives EN/FAULT pin. Thermal Fault, Output Disabled,			1.9	V
I _{IL} _{EN/FAULT}	Logic Low Input Sink Current	V _{EN} = GND at the normal operation		10		μA
		V _{EN} = GND at the thermal shutdown		20		μA

Symbol	Parameters	Test Conditions/Comments	Min	Typ	Max	Units
I _{HEN/FAULT}	Logic High Leakage Current	V _{EN} = 4.3V			1	μA
DEVSLPOUTB						
V _{PGPD}	Pull-down Voltage	I _{SINK} = 4mA, sinking current into DEVSLPOUTB			0.3	V
I _{PGLEAK}	Leakage Current	V _{DEVSLPOUTB} = 1.8V			1	μA
FET_ON (Note 3)						
	Logic threshold low-to-mid		0.3	0.5	0.7	V
	Logic threshold mid-to-high		0.8	1.0	1.2	V
	Input leakage current	FET_ON = GND			1	μA
Total Device						
I _{Q_OP}	Bias Current	Operational		165	250	μA
I _{Q_DIS}		Disable (EN/FAULT = GND or DEVSLP = High)		104		μA
I _{Q_FLT}		Thermal Fault Latch Off		100		μA
V _{MIN}	Minimum Operating Voltage	(Note 4)			4.2	V
	Reverse Bias Leakage Current	V _{CC} = GND, V _{OUT} = 5V		4		μA

Note: 1. Guaranteed by Design

Note: 2. Pulse test: Pulse width = 300μs, Duty cycle = 2%.

Note: 3. Total pin capacitance must be ≤50pf to be considered floating by the chip.

Note: 4. Device may shut down prior to reaching this level based on actual UVLO trip point.

Theory of Operation / Application Information

DevSleep Logic Operation

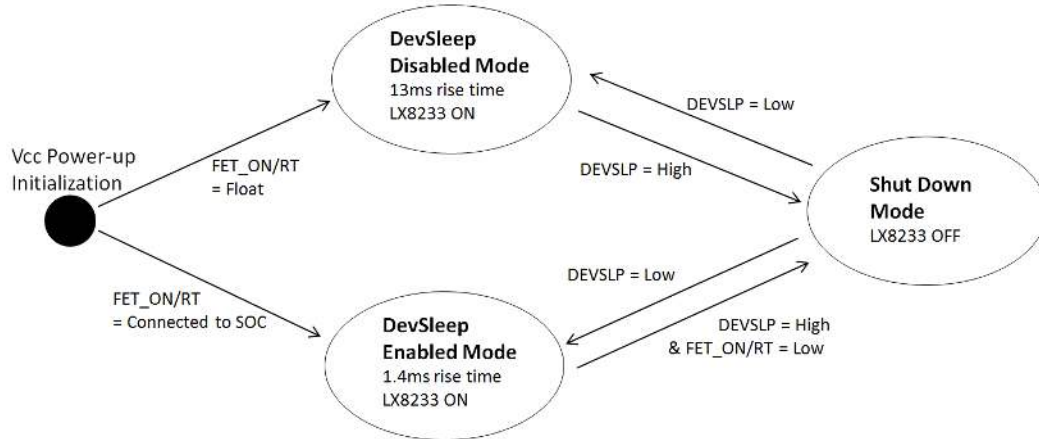


Figure 5 · DevSleep Operation

VCC Power-up Initialization: As VCC rises the LX8233 initializes its internal circuits. Upon reaching the UVLO threshold the LX8233 also detects the status of FET_ON pin. If FET_ON detects a float condition it initializes in DevSleep Disabled Mode. However if FET_ON is detected as connected to SOC then it initializes to DevSleep Enabled Mode.

DevSleep Disabled Mode: When VCC reaches the UVLO threshold, VOUT slews for 13ms from 0V to VCC. The LX8233 is monitoring the DEVSLP pin and enters Shutdown Mode. if DEVSLP goes high.

DevSleep Enabled Mode: When VCC reaches the UVLO threshold, VOUT slews for 1.4ms from 0V to VCC. In this mode, the LX8233 is monitoring both the DEVSLP and FET_ON pins. When both DEVSLP goes high and FET_ON goes low, LX8233 enters Shutdown Mode.

Shut Down Mode: Once LX8233 enters this mode the chip shuts down VOUT and most internal circuitry minimizing quiescent current to that required to monitor the DEVSLP pin and maintain state information. When DEVSLP toggles low, the LX8233 restores itself to original DevSleep Disabled/Enabled Mode operation mode.

EN/FAULT Operation

EN/FAULT is typically floated and connected as common node between the parallel connected devices. There is an a weak (~430kΩ) internal pull-up resistor, so the EN/FAULT pin goes to ~4.3V when VCC = 5V. However when parallel connected the actual voltage depends on the mismatch between the internal regulator supply voltages. To disable VOUT using the EN/FAULT pin you must use an external pull-down device, however the internal pull-up resistor will enable VOUT without any external signal.

If the IC's junction temperature passes the thermal shutdown threshold the LX8233 will pull down the EN/FAULT pin to the mid-level fault logic condition. As shown in the simplified schematic below an internal switch (thermal latch) engages at thermal shutdown driving the EN/FAULT pin to approximately 1.6V with pulldown capability to drive several parallel connected devices. Thus if LX8233 reaches thermal shutdown it will latch off all the parallel connected devices on the same

node. It remains at 1.6V until either the Enable Pin is pulled low then left to float, the DEVSLP pin is toggled (high then low, or low to high), or there is a VCC power recycle.

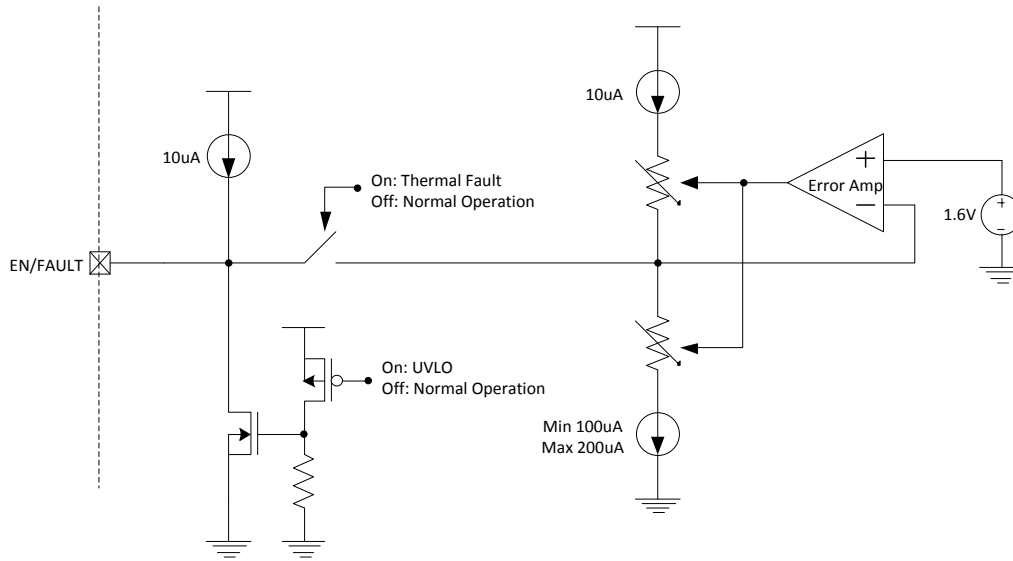
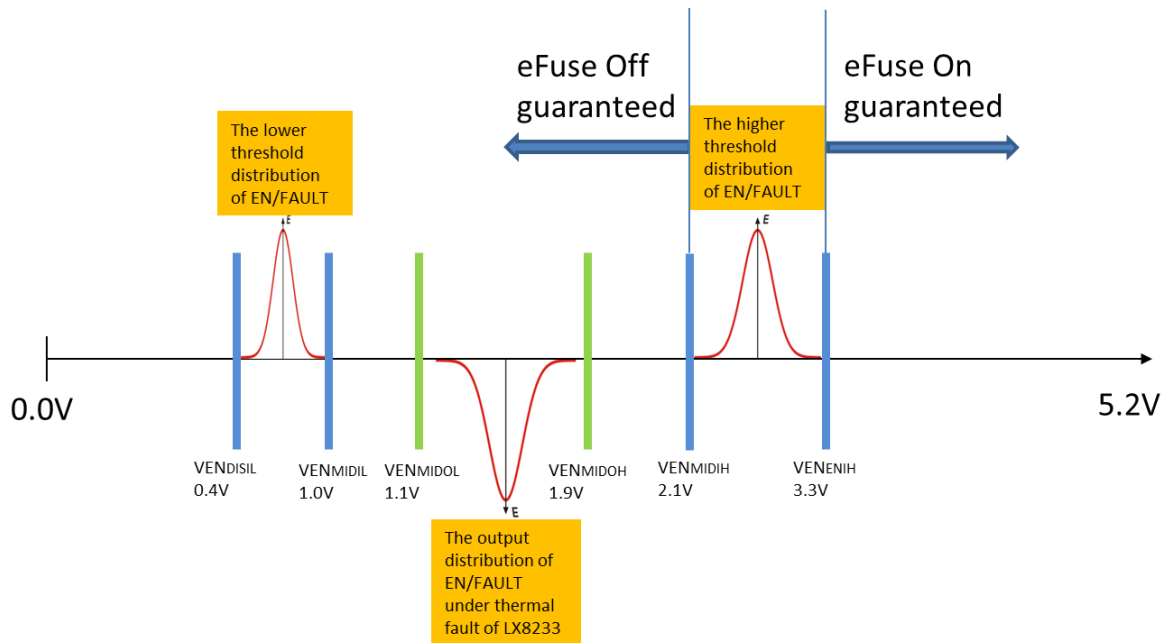


Figure 6 · Simplified EN/FAULT circuitry

IReverse	UVLO	DEVSLP	THERM	ENABLE
0	0	0	0	1
0	0	0	1	mid
0	0	1	0	0
0	0	1	1	0
0	1	0	0	0
0	1	0	1	0
0	1	1	0	0
0	1	1	1	0
1	0	0	0	0
1	0	0	1	0
1	0	1	0	0
1	0	1	1	0
1	1	0	0	0
1	1	0	1	0
1	1	1	0	0
1	1	1	1	0

EN/FAULT node is share with a secondary eFuse in order to shutdown the secondary eFuse for the case SAS-Disable or DevSleep mode, thermal fault and UVLO condition. It will guarantee the secondary eFuse never turns on when LX8233 is under the specific condition like SAS-Disable, DevSleep, thermal fault and UVLO conditions. The EN/FAULT responses are listed in the following table.

	eFuse	EN/FAULT as OUTPUT	Effect on the secondary part
UVLO	eFuse is turned off.	Ground. Drive EN/FAULT is lower than 0.4V	Disable the secondary part.



Thermal Fault	eFuse is turned off. The thermal shutdown is latched off. It can be reset by VIN recycle, DEVSLP toggle or EN/FAULT toggle.	Mid point. Drive EN/FAULT lower than 1.9V higher than 1.1V	Disable the secondary part.
DEVSLP (SAS-DISABLE)	eFuse is turned off.	Ground. Drive EN/FAULT is lower than 0.4V	Disable the secondary part.

Reverse Current Protection

While the simplest protection against a reverse current condition may be a diode in series connection to the load, this method has drawbacks. There is significant power loss in the forward conduction mode, as well as poor supply rail regulation. In order to solve this problem, the LX8233 implements a bidirectional voltage and current blocking FET switch. The basic concept of this method is to detect the polarity of voltage drop through the FET pass device and open up the switch to block reverse current. This method is very effective for fast slew rate of reverse current blocking. If the slew rate of the reverse current is slower than a certain rate (i.e. a slowly reducing input voltage), the reverse current will be allowed until the input voltage reaches the UVLO threshold. Below this level, the switch is quickly turned off and blocks reverse current and voltage.

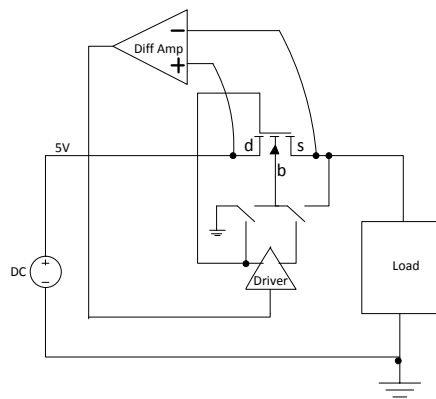


Figure 7 · Simplified reverse current detection circuitry

Under-Voltage Lock-Out

In LX8233, UVLO plays an important role. It has a high threshold with very little hysteresis and a very fast comparator propagation delay. These features of UVLO circuit maximize the reverse current blocking function capability.

UVLO	EN/FAULT	DEVSLP	FET_ON	LX8233	DEVSLPOUTB with pullup
violated	*	*	*	off	off/high

Package Outline Dimensions

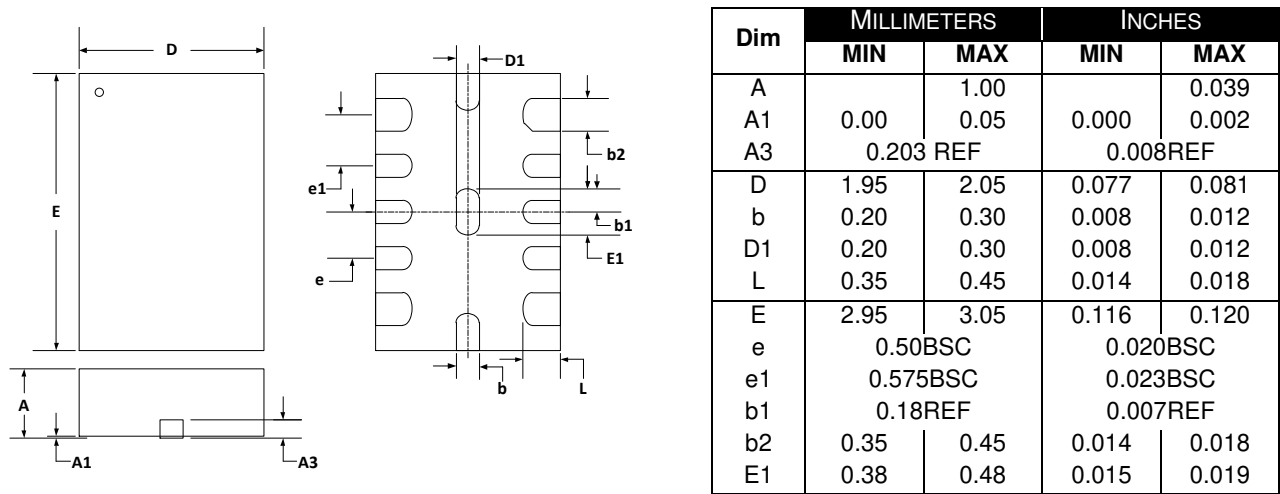


Figure 8 · LQ 12-Pin VQFN Package Dimensions

Note: 1. Dimensions do not include mold flash or protrusions; these shall not exceed 0.155mm (.006”) on any side. Lead dimension shall not include solder coverage.

Note: 2. Dimensions are in mm, inches are for reference only.

Land Pattern Recommendation

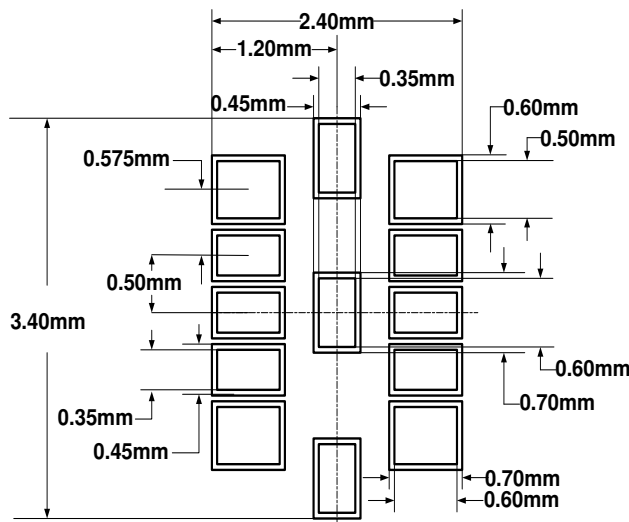


Figure 9 · LQ 12-Pin VQFN Package Land Pattern

Disclaimer:

This PCB land pattern recommendation is based on information available to Microsemi by its suppliers. The actual land pattern to be used could be different depending on the materials and processes used in the PCB assembly, end user must account for this in their final layout. Microsemi makes no warranty or representation of performance based on this recommended land pattern



Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

E-mail: sales.support@microsemi.com

© 2014 Microsemi Corporation. All rights reserved. Microsemi and the Microsemi logo are trademarks of Microsemi Corporation. All other trademarks and service marks are the property of their respective owners.

Microsemi Corporation (Nasdaq: MSCC) offers a comprehensive portfolio of semiconductor and system solutions for communications, defense & security, aerospace and industrial markets. Products include high-performance and radiation-hardened analog mixed-signal integrated circuits, FPGAs, SoCs and ASICs; power management products; timing and synchronization devices and precise time solutions, setting the world's standard for time; voice processing devices; RF solutions; discrete components; security technologies and scalable anti-tamper products; Power-over-Ethernet ICs and midspans; as well as custom design capabilities and services. Microsemi is headquartered in Aliso Viejo, Calif., and has approximately 3,400 employees globally. Learn more at www.microsemi.com.

Microsemi makes no warranty, representation, or guarantee regarding the information contained herein or the suitability of its products and services for any particular purpose, nor does Microsemi assume any liability whatsoever arising out of the application or use of any product or circuit. The products sold hereunder and any other products sold by Microsemi have been subject to limited testing and should not be used in conjunction with mission-critical equipment or applications. Any performance specifications are believed to be reliable but are not verified, and Buyer must conduct and complete all performance and other testing of the products, alone and together with, or installed in, any end-products. Buyer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the Buyer's responsibility to independently determine suitability of any products and to test and verify the same. The information provided by Microsemi hereunder is provided "as is, where is" and with all faults, and the entire risk associated with such information is entirely with the Buyer. Microsemi does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other IP rights, whether with regard to such information itself or anything described by such information. Information provided in this document is proprietary to Microsemi, and Microsemi reserves the right to make any changes to the information in this document or to any products and services at any time without notice.